

# M24M02

# I<sup>2</sup>C-Compatible (2-wire) Serial EEPROM 2-Mbit (262,144 x 8)

### **DATASHEET**

#### **Features**

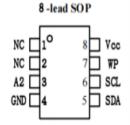
- Low Voltage and Standard Voltage Operation Available
  - 1.7V (V<sub>CC</sub> = 1.7V to 5.5V)
- Internally Organized 262,144 x 8 (2-Mbit, 256-Kbyte)
- I<sup>2</sup>C-Compatible (2-wire) Serial Interface
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- Bidirectional Data Transfer Protocol
- Write Protect Pin for Full Array Hardware Data Protection
- 256-byte Page Write Mode

Byte Write and Partial Page Writes Allowed

- Self-timed Write Cycle
  - Random and Sequential Read Modes
- High Reliability
  - Byte Write within 8 ms
  - Data retention: 100 years
- Green Package Options (Lead-free/Halide-free/RoHS Compliant)
  8-lead JEDEC SOIC and Thin or Standard Thickness 8-ball WLCSP
- Die Sale Options: Wafer Form and Tape and Reel Available

## **Description**

The M24M02 provides 2,097,152 bits of Serial Electrically Erasable and Programmable Read-Only Memory (EEPROM) organized as 262,144 words of 8 bits each. The device's cascadable feature allows up to two devices to share a common 2-wire bus. The device is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential. The device is available in space-saving 8-lead JEDEC SOIC and 8-ball packages.



### Examples

型号	封装	私印	工作电压
M24M02-DRMN6TP-TUDI	SOP8	24M02DR	1.7to 5.5



# )Pin Descriptions

Pin Name	Type	Functions
A2	I	Address Inputs
SDA	I/O	Serial Data
SCL	I	Serial Clock Input
WP	I	Write Protect
GND	P	Ground
Vcc	Р	Power Supply

Table 1

Position	A	В	С	D
1	-	-	SCL	-
2	$V_{CC}$	WP	-	SDA
3	NC	-	-	$V_{SS}$
4	-	NC	A2	-

Table 2

# **Block Diagram**

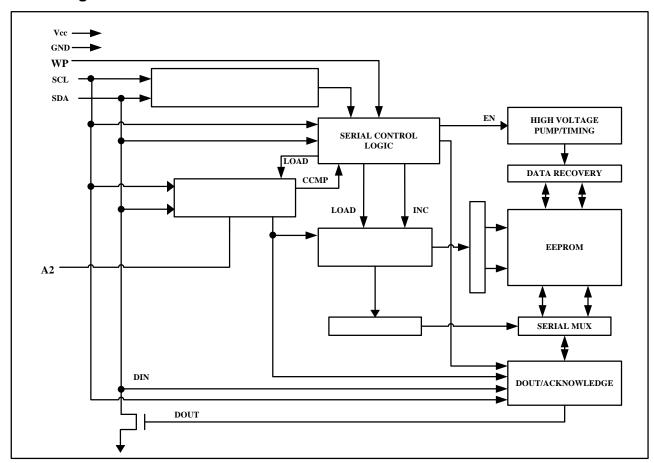


Figure 1

DEVICE/PAGE ADDRESSES (A2): The A2 pin is device address inputs that are hard wire for the M24M02. Two 2M devices may be addressed on a single bus system (device addressing is discussed in detail under the Device Addressing section).

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SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-ORed with any number of other open-drain or open- collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The M24M02has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to Vcc, the write protection feature is enabled and operates as shown in the following **Table 3**.

WP Pin Status	M24M02
At VCC	Full(2048K)Array
At GND	Normal Read/Write Operations

Table 3

### **Functional Description**

### 1. Memory Organization

M24M02, 2M SERIAL EEPROM: Internally organized with 1024 pages of 256 bytes each, the 2M requires a 18 -bit data word address for random word addressing.

### 2. Device Operation

CLOCK and DATA TRANSITIONS: The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see **Figure 2**). Data changes during SCL high periods will indicate a start or stop condition as defined below.

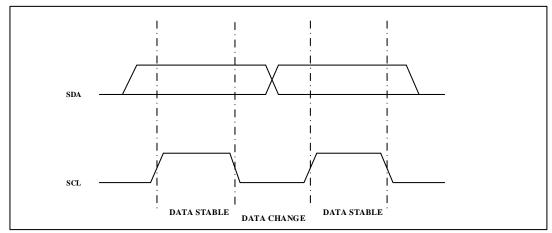


Figure 2. Data Validity

START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see **Figure 3**).

STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see **Figure 3**).

ACKNOWLEDGE: All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

STANDBY MODE: The M24M02features a low-power standby mode which is enabled: (a) upon power-up and (b) after the receipt of the STOP bit and the completion of any internal operations.

MEMORY RESET: After an interruption in protocol, power loss or system reset, any two-wire part can be reset by following these steps:

- 1. Clock up to 9 cycles.
- 2. Look for SDA high in each cycle while SCL is high.
- 3. Create a start condition.



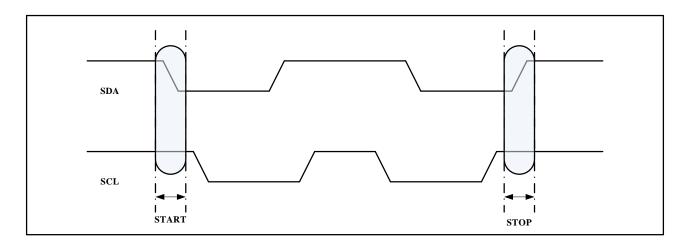


Figure 3. Start and Stop Definition

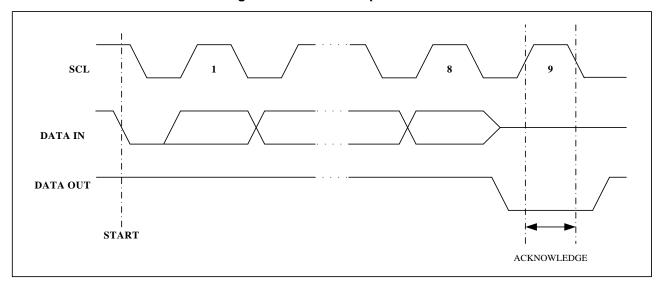


Figure 4. Output Acknowledge



#### 3. Device Addressing

The 2M EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see **Figure 5**)

The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices.

The 2M EEPROM uses A2 device address bit and one world address bit to allow as much as two devices on the same bus. This device address bit must be compared to their corresponding hardwired input pins. The A2 pin uses an internal proprietary circuit that biases them to a logic low condition if the pins are allowed to float.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

MSB							LSB
1	0	1	0	A2	B17	B16	R/W
B15	B14	B13	B12	B11	B10	В9	B8
B7	В6	В5	B4	В3	B2	B1	В0

Figure 5. Device Address and two 8-bit data word address

DATA SECURITY: The M24M02has a hardware data protection scheme that allows the user to write protect the entire memory when the WP pin is at VCC.



#### 4. Write Operations

BYTE WRITE: A write operation requires two 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, tWR, to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see **Figure 6**).

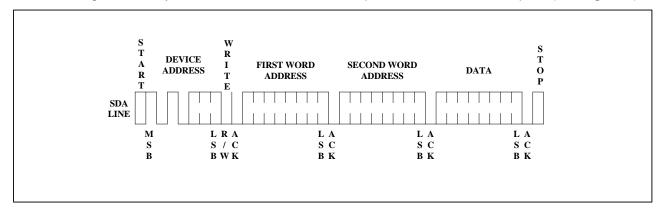


Figure 6. Byte Write

PAGE WRITE: The Page Write mode allows up to 256 bytes to be written in a single Write cycle. A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to 255 more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition. (see **Figure 7**).

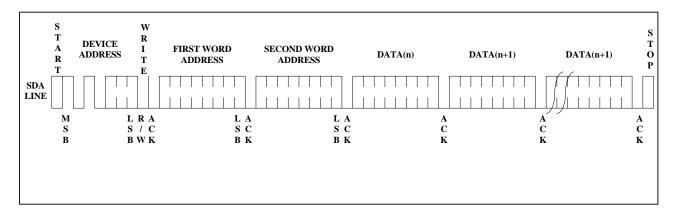


Figure 7. Page Write

The data word address lower eight bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than 256 data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

WRITE IDENTIFICATION PAGE: The Identification Page (256 bytes) is an additional page which can be written and (later) permanently locked in Read-only mode. It is written by issuing the Write Identification Page instruction. This instruction uses the same protocol and format as Page Write (into memory array), except for the following differences:

- Device type identifier = 1011b
- MSB address bits B17/B8 are don't care except for address bit B10 which must be "0".
  LSB address bits B7/B0 define the byte address inside the Identification page.



M24M02 2M bits (262,144x8)

If the Identification page is locked, the data bytes transferred during the Write Identification Page instruction are not acknowledged (NoAck).

LOCK IDENTIFICATION PAGE: The Lock Identification Page instruction (Lock ID) permanently locks the Identification page in Read-only mode. The Lock ID instruction is similar to Byte Write (into memory array) with the following specific conditions:

Device type identifier = 1011b

Address bit B10 must be '1'; all other address bits are don't care

The data byte must be equal to the binary value xxxx xx1x, where x is don't care

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.



#### 5. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

#### **CURRENT ADDRESS READ:**

The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see **Figure 8**).

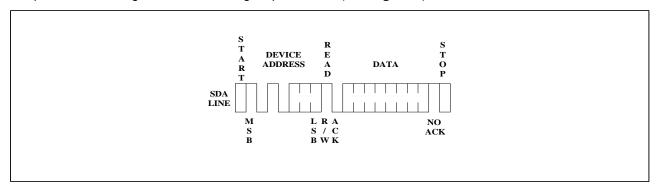


Figure 8. Current Address Read

#### RANDOM READ:

A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 9**)

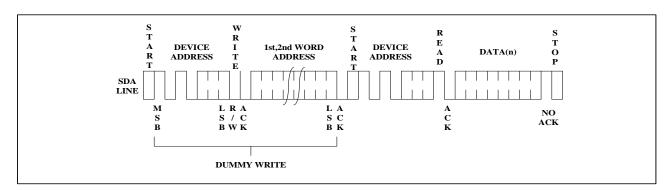


Figure 9. Random Read





SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see **Figure 10**).

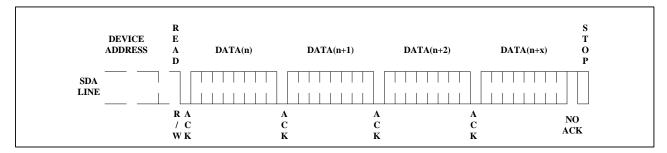


Figure 10. Sequential Read

READ IDENTIFICATION PAGE: The Identification Page (256 bytes) is an additional page which can be written and (later) permanently locked in Read-only mode.

The Identification Page can be read by issuing an Read Identification Page instruction. This instruction uses the same protocol and format as the Random Address Read (from memory array) with device type identifier defined as 1011b. The MSB address bits B17/B8 are don't care, the LSB address bits B7/B0 define the byte address inside the Identification Page. The number of bytes to read in the ID page must not exceed the page boundary (e.g.: when reading the Identification Page from location 10d, the number of bytes should be less than or equal to 246, as the ID page boundary is 256 bytes)



### **Electrical Characteristics**

Absolute Maximum Stress Ratings:

•	DC Supply Voltage	0.3V to +6.5V
•	Input / Output Voltage	GND-0.3V to VCC+0.3V
•	Storage Temperature	5°C to +120°C
•	Electrostatic pulse (Human Body model)	8000V

#### Comments:

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

#### **DC Electrical Characteristics**

Applicable over recommended operating range from (unless otherwise noted):

M24M02	TA =	-00°C to +	85℃				
M24M02E1	TA =	-40°C to +	105℃	VCC = +2.8V to +5.5V CL=100 pF			
M24M02E0	TA =	-40°C to +	125℃		о р.		
Parameter		Symbol	Min	Тур	Max	Unit	Condition
Supply Voltage		VCC1	2.8	ı	5.5	<b>V</b>	-
Supply Current VCC=5.0	V	ICC1	-	0.26	1.0	mΑ	READ at 400KHZ
Supply Current VCC=5.0	V	ICC2	-	0.56	2.0	mA	WRITE at 400KHZ
Supply Current VCC=5.0	V	ISB1	-	0.03	0.5	μΑ	VIN=VCC or VSS
Input Leakage Current		IL1	-	0.10	1.0	μΑ	VIN=VCC or VSS
Output Leakage Current		ILO	-	0.05	1.0	μΑ	VOUT=VCC or VSS
Input Low Level		VIL1	-0.3	ı	VCC×0.3	V	VCC=1.7V to 5.5V
Input High Level		VIH1	VCC×0.7	-	VCC+0.3	V	VCC=1.7V to 5.5V
Output Low Level VCC=	1.7V	VOL1	-	•	0.2	V	IOL=2.1mA
Output Low Level VCC=	5.0V	VOL2	-	-	0.4	V	IOL=3.0mA

Table 4

### Pin Capacitance

Applicable over recommended operating range from TA = 25°C, f = 1.0 MHz, VCC = +2.8V

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Input/Output Capacitance(SDA)	Cıo	-	-	8	рF	Vio=0V
Input Capacitance(A2,SCL)	Cin	-	-	6	pF	Vin=0V

Table 5



#### **AC Electrical Characteristics**

Applicable over recommended operating range from (unless otherwise noted):

M24M02	TA =-40°C to +85°C	
M24M02E1	TA =-40°C to +105°C	VCC = +2.8V to +5.5V CL=100 pF
M24M02E0	TA =-40°C to +125°C	

Parameter	Symbol	2.8V	2.8V≤VCC < 5.5V		
raianietei	Symbol	Min	Тур	Тур Мах	
Clock Frequency,SCL	fSCL	-	-	1000	kHz
Clock Pulse Width Low	tLOW	0.5	-	-	μs
Clock Pulse Width High	tHIGH	0.26	-	-	μs
Noise Suppression Time	tl	-	-	50	ns
Clock Low to Data Out Valid	tAA	-	-	0.45	μs
Time the bus must be free before a new transmission can start	tBUF	0.5	-	-	μs
Start Hold Time	tHD:STA	0.25	-	-	μs
Start Setup Time	tSU:STA	0.25	-	-	μs
Data In Hold Time	tHD:DAT	0	-	-	μs
Data in Setup Time	tSU:DAT	100	-	-	ns
Input Rise Time(1)	tR	-	-	0.12	μs
Input Fall Time(1)	tF	-	-	0.12	μs
Stop Setup Time	tSu:STO	0.25	-	-	μs
Data Out Hold Time	tDH	50	-	-	ns
Write Cycle Time	tWR	-		8	ms
5.0V,25°C,Byte Mode(1)	Endurance	-	1M	-	Write Cycle

#### Table 6

### Notes:

1. This parameter is characterized and is not 100% tested.

2. AC measurement conditions: RL (connects to VCC): 1.3 k

Input pulse voltages: 0.3 VCC to 0.7 VCC

Input rise and fall time: 50 ns

Input and output timing reference voltages: 0.5 VCC

The value of RL should be concerned according to the actual loading on the user's system.

3. The device uses ECC (Error Correction Code) logic with 6 ECC bits to correct one bit error in 4 data bytes. Therefore, when a single byte has to be written, 4 bytes (including the ECC bits) are re-programmed. It is recommended to write by multiple of 4 bytes located at addresses 4N, 4(N+1), 4(N+2), 4(N+3), in order to benefit from the maximum number of write cycles.



#### )Bus Timing

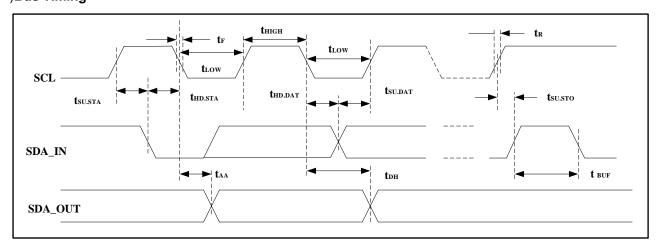


Figure 11. SCL: Serial Clock, SDA: Serial Data I/O

#### Write Cycle Timing

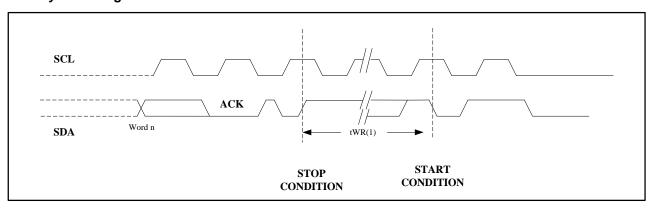


Figure 12. SCL: Serial Clock, SDA: Serial Data I/O

#### Notes:

The write cycle time tWR is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.

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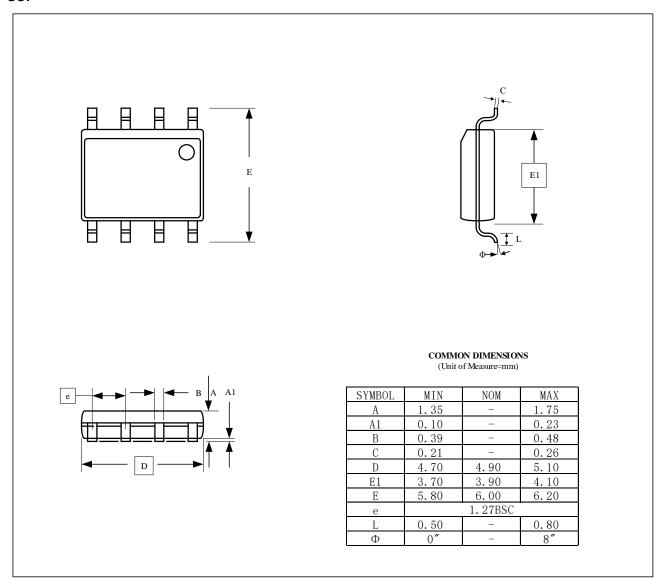
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### **Package Information**

#### SOP



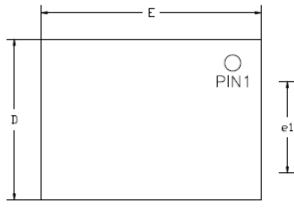
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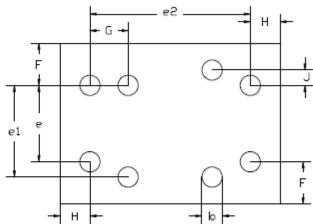
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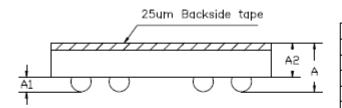
#### **WLCSP8**





TOP VIEW (MARK SIDE)

(BALL SIDE)



# COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX		
Α	0.490	0.540	0.590		
A1	0.165	0.190	0.215		
A2	0.325	0.350	0.375		
D	2.080	2.100	2.120		
e1	1.200BSC				
Ш	2.860	2.880	2.900		
e2		2.100BSC			
Ф	0.240	0.270	0.300		
G	0.500BSC				
е	1.000BSC				
I	0.390 REF				
ᄕ	0.550 REF				
J		0.200 REF	-		

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## )Marking Diagram

SOP

M24M02

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